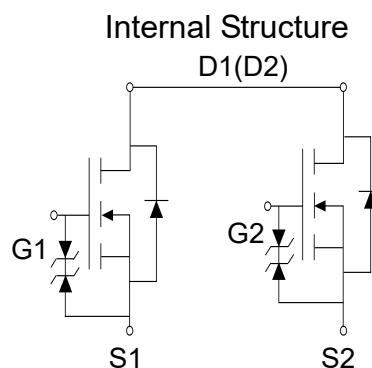


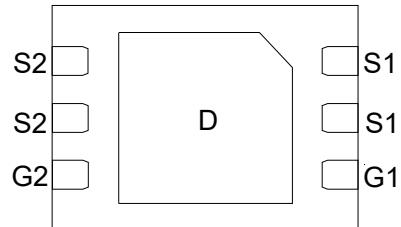
Description

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

| MOSFET Product Summary | | |
|------------------------|--------------------------|--------------------|
| V _{DS} (V) | R _{DS(on)} (mΩ) | I _D (A) |
| 20 | 6.0@ VGS=4.5V | 12 |
| | 7.5@ VGS=3.8V | |
| | 9.2@ VGS=2.5V | |



Top View(DFN2*3-6L)



Absolute maximum rating@25°C

| Parameter | Symbol | Maximum | Units |
|--|-----------------------------------|------------|-------|
| Drain-Source Voltage | V _{DS} | 20 | V |
| Gate-Source Voltage | V _{GS} | ±12 | V |
| Drain Current-Continuous | I _D | 12 | A |
| Drain Current-Pulsed (Note 1) | I _{DM} | 70 | A |
| Maximum Power Dissipation | P _D | 1.5 | W |
| Operating Junction and Storage Temperature Range | T _J , T _{STG} | -55 to 150 | °C |

Thermal Characteristic

| Parameter | Typical | Maximum | Units |
|---|------------------|---------|-------|
| Thermal Resistance,Junction-to-Ambient (Note 2) | R _{θJA} | 83 | °C/W |

Electrical characteristics per line@25°C(unless otherwise specified)

| Parameter | Symbol | Conditions | Min. | Typ. | Max. | Units |
|----------------------------------|--------------|--|------|------|----------|-----------|
| Drain-Source Breakdown Voltage | BV_{DSS} | $I_D = 250\mu A, V_{GS} = 0V$ | 20 | | - | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 20V, V_{GS} = 0V$ | - | - | 1 | μA |
| Gate-Body Leakage Current | I_{GS} | $V_{DS} = 0V, V_{GS} = \pm 12V$ | - | - | ± 10 | μA |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 0.45 | 0.8 | 1.2 | V |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = 4.5V, I_D = 5.5A$ | | 6.0 | 7.5 | $m\Omega$ |
| | | $V_{GS} = 3.8V, I_D = 5.5A$ | | 7.5 | 8.5 | |
| | | $V_{GS} = 2.5V, I_D = 5.0A$ | | 9.2 | 11 | |
| Forward Transconductance | G_F | $V_{DS} = 5V, I_D = 5A$ | | 20 | | S |
| Input Capacitance | C_{iss} | $V_{GS} = 0V, V_{DS} = 10V, f = 1MHz$ | - | 1310 | | pF |
| Output Capacitance | C_{oss} | | - | 264 | | pF |
| Reverse Transfer Capacitance | C_{rss} | | - | 235 | | pF |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 10V, R_{GEN} = 3\Omega, V_{GS} = 5V, R_L = 1.35\Omega$ | - | 6 | | nS |
| Turn-On Rise Time | t_r | | - | 13 | | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 52 | | nS |
| Turn-Off Fall Time | t_f | | - | 16 | | nS |
| Total Gate Charge | Q_g | $V_{DS} = 10V, I_D = 7A, V_{GS} = 4.5V$ | | 15 | | nC |
| Gate-Source Charge | Q_{gs} | | | 0.8 | | nC |
| Gate-Drain Charge | Q_{gd} | | | 3.2 | | nC |
| Diode Forward Voltage | V_{SD} | $V_{GS} = 0V, I_S = 1A$ | | | 1.2 | V |
| Diode Forward Current | I_S | | | | 7 | A |

Note 1: Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2: Surface Mounted on FR4 Board, $t \leq 10$ sec.

Typical Characteristics

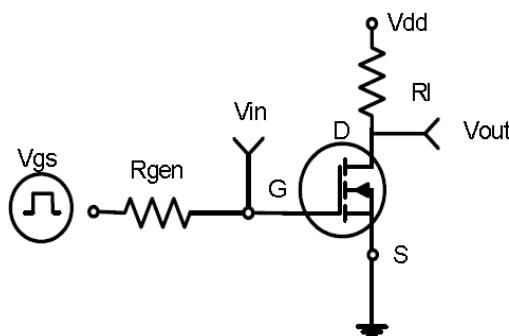


Fig 1. Switching Test Circuit

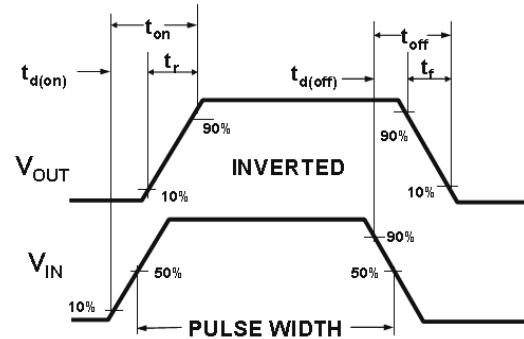


Fig 2. Switching Waveforms

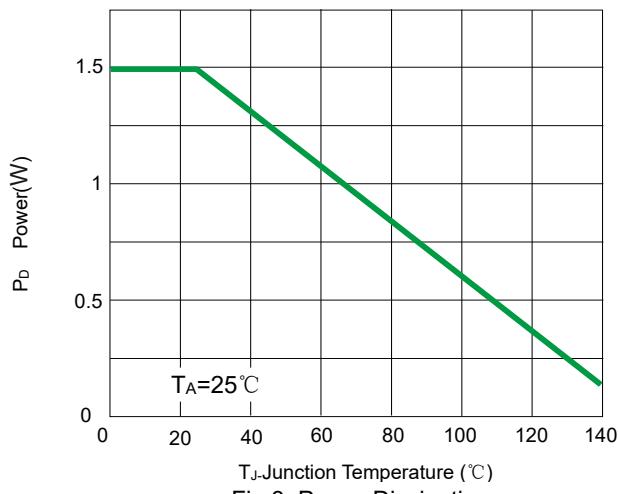


Fig 3. Power Dissipation

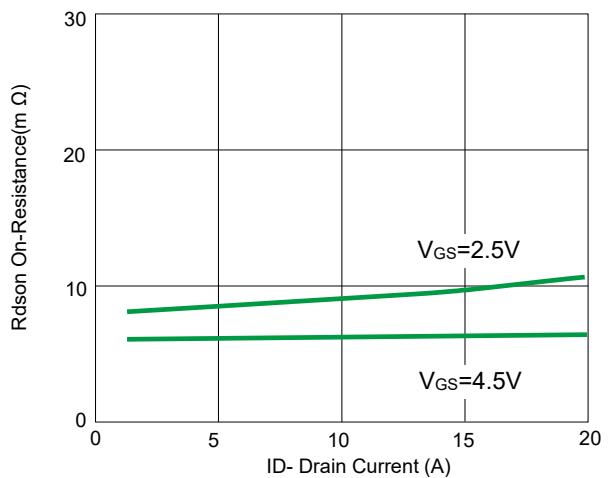


Fig 4. Transfer Characteristics

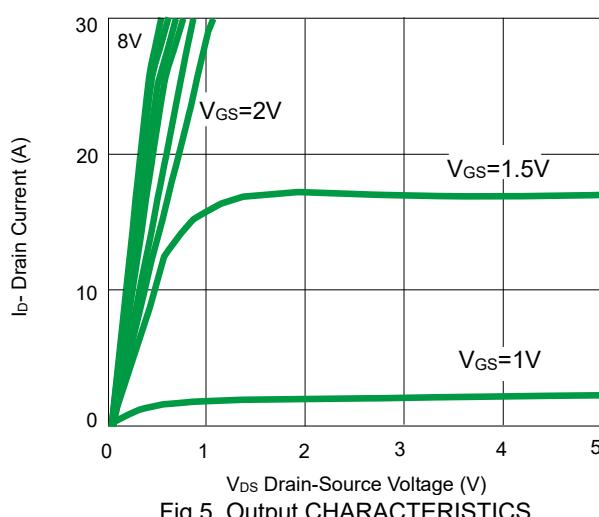


Fig 5. Output CHARACTERISTICS

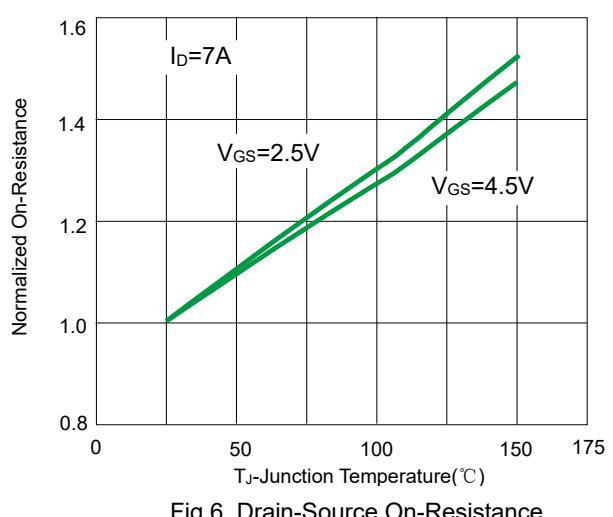


Fig 6. Drain-Source On-Resistance

Dual N-Channel MOSFET

PDNM6N20V12E

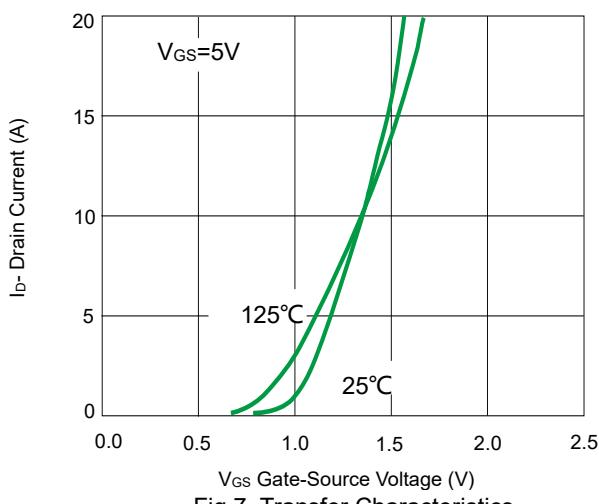


Fig 7. Transfer Characteristics

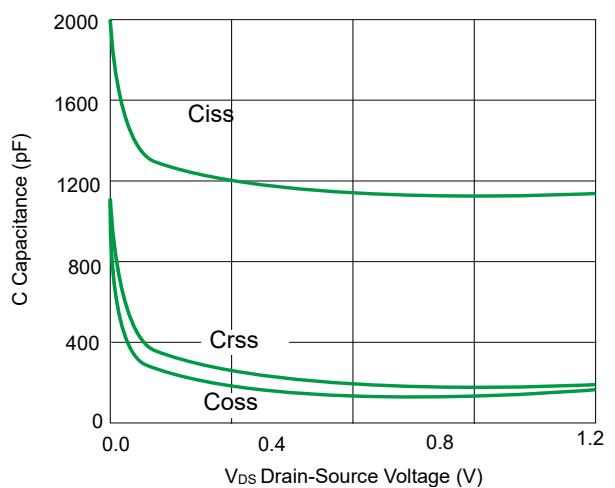


Fig 8. Capacitance vs V_{DS}

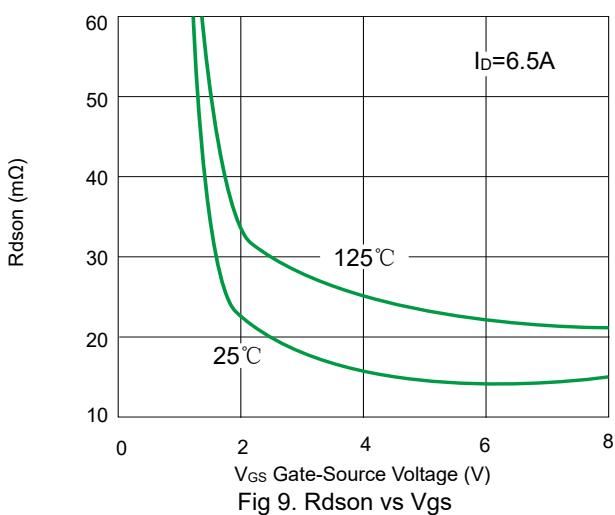


Fig 9. $R_{ds(on)}$ vs V_{GS}

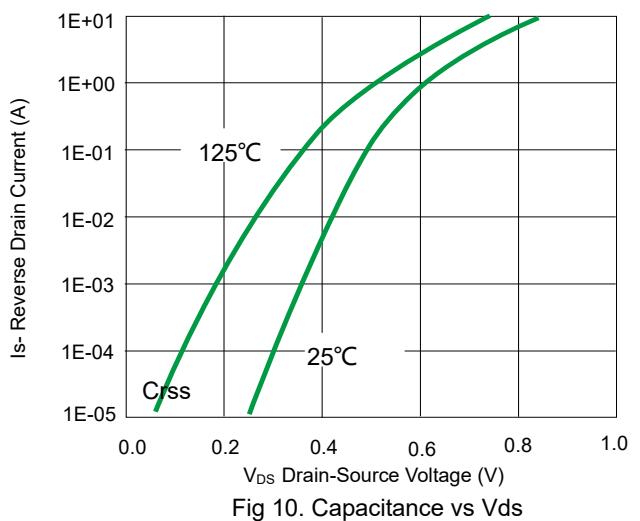


Fig 10. Capacitance vs V_{DS}

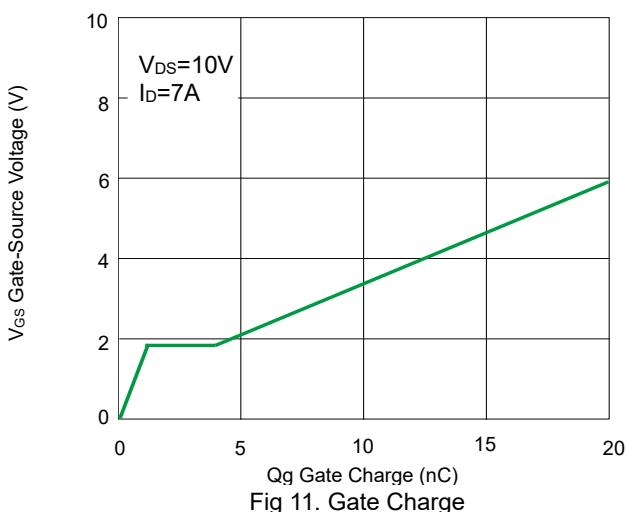


Fig 11. Gate Charge

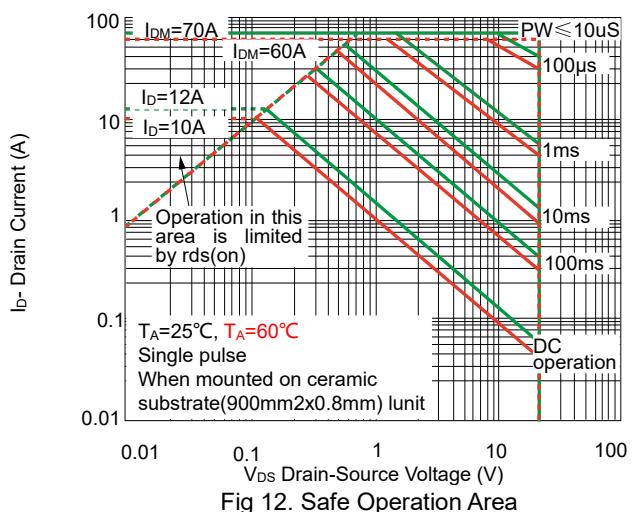


Fig 12. Safe Operation Area

Dual N-Channel MOSFET

PDNM6N20V12E

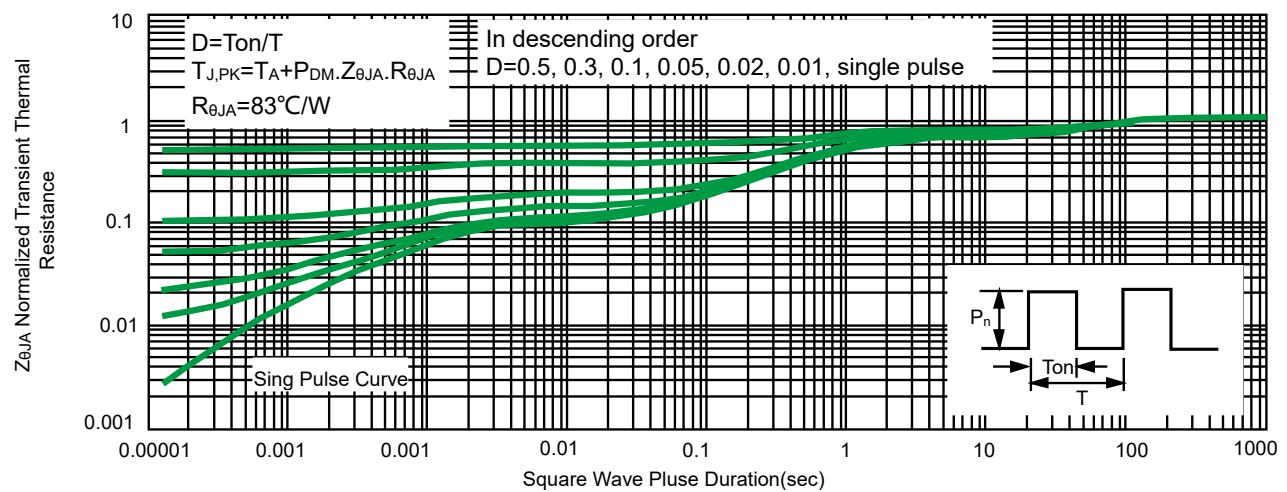
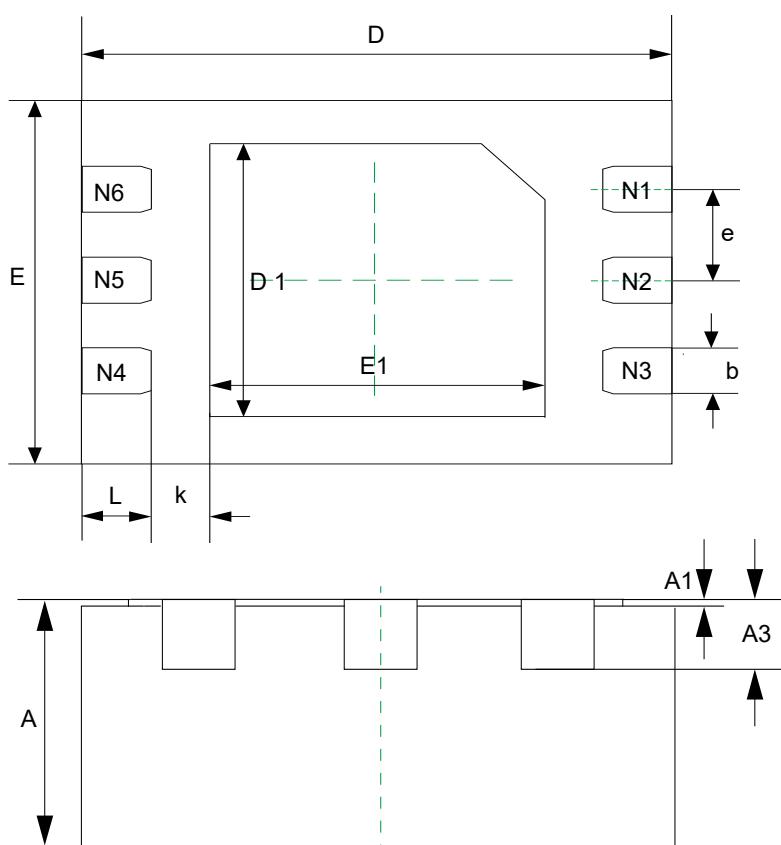


Fig 14 Normalized Maximum Transient Thermal Impedance

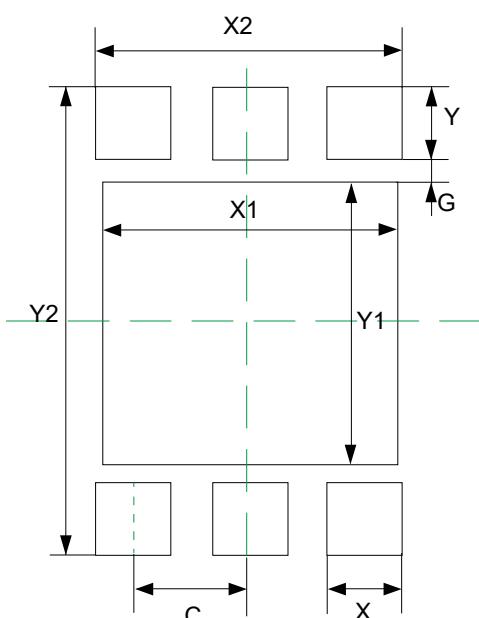
Product dimension(DFN2*3-6L)



Dual N-Channel MOSFET

PDNM6N20V12E

| Dim | Millimeters | | Inches | |
|-----|-------------|-------|----------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.700 | 0.800 | 0.028 | 0.031 |
| A1 | 0.000 | 0.050 | 0.000 | 0.002 |
| A3 | 0.203REF | | 0.008REF | |
| D | 2.950 | 3.050 | 0.116 | 0.120 |
| E | 1.950 | 2.050 | 0.077 | 0.081 |
| D1 | 1.450 | 1.550 | 0.057 | 0.061 |
| E1 | 1.650 | 1.750 | 0.065 | 0.069 |
| k | 0.200MIN | | 0.008MIN | |
| b | 0.200 | 0.300 | 0.008 | 0.012 |
| e | 0.500TYP | | 0.020TYP | |
| L | 0.300 | 0.400 | 0.012 | 0.016 |



| Dim | Millimeters |
|-----|-------------|
| C | 0.650 |
| G | 0.150 |
| X | 0.400 |
| X1 | 1.600 |
| X2 | 1.700 |
| Y | 0.530 |
| Y1 | 1.940 |
| Y2 | 3.300 |

Ordering information

| Device | Package | Shipping |
|--------------|---------------------|--------------------|
| PDNM6N20V12E | DFN2*3-6L (Pb-Free) | 3000 / Tape & Reel |

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